

CHONGQING CLOUDCHILD TECHNOLOGY CO., LTD

SOT-23-3L Plastic-Encapsulate MOSFETS

CC3400A N-Channel Enhancement Mode Field Effect Transistor

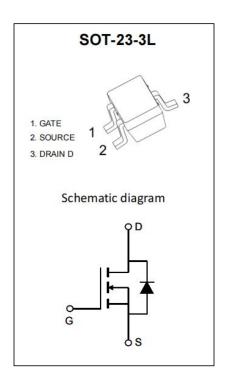
V _{(BR)DSS}	R _{DS(on)TYP}	ΙD
	20mΩ@10V	
30 V	22mΩ@4.5V	5.8A
	25mΩ@2.5V	

FEATURE

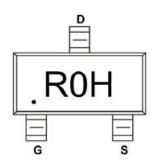
- TrenchFET Power MOSFET
- Excellent R_{DS(ON)} and Low Gate Charge
- AEC Q101 Qualified

APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter
- Battery Switching



MARKING



Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	V _{DS}	30	V	
Gate-Source Voltage	V _{GS}	±12	V	
Continuous Drain Current	I _D	5.8	А	
Pulsed Drain Curren ⁽¹⁾	I _{DM}	30	А	
Power Dissipation	P _D	0.4	W	
Thermal Resistance from Junction to Ambient ⁽²⁾	$R_{ heta JA}$	313	°C/W	
Junction Temperature	TJ	150	$^{\circ}$	
Storage Temperature	T _{STG}	-55~ +150	$^{\circ}$ C	

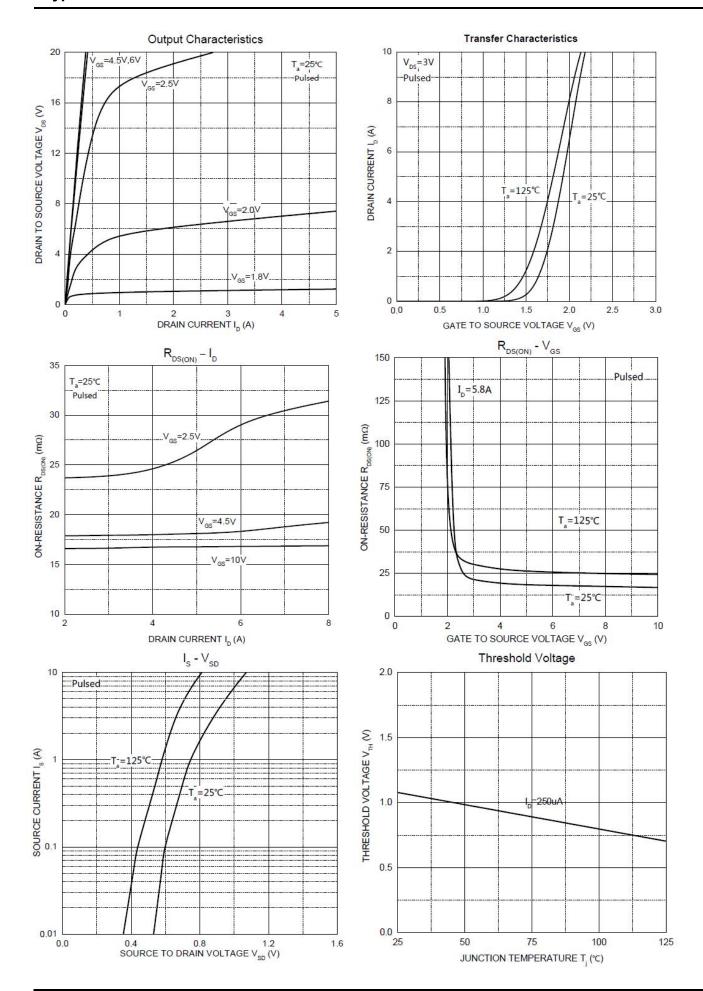
MOSFET ELECTRICAL CHARACTERISTICS

T_a=25 °C unless otherwise specified

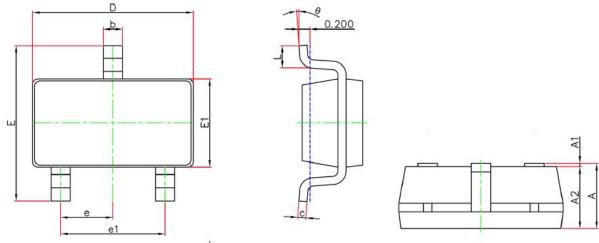
Parameter	Symbol	Test Condition	Min	Туре	Max	Unit	
Static Characteristics		•	•				
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	30			V	
Zero gate voltage drain current	I _{DSS}	V _{DS} =24V,V _{GS} = 0V			1	μA	
Gate-body leakage current	I _{GSS}	V _{GS} =±12V, V _{DS} = 0V			±0.1	μA	
Gate threshold voltage ⁽³⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.7	1.0	1.4	V	
		V _{GS} =10V, I _D =5.8A		20	27		
Drain-source on-resistance ⁽³⁾	R _{DS(on)}	V _{GS} =4.5V, I _D =5A		22	30	$m\Omega$	
		V _{GS} =2.5V, I _D =4A		25	48		
Forward tranconductance ⁽³⁾	g FS	V _{DS} =5V, I _D =5A	8			S	
Dynamic characteristics ⁽⁴⁾	•	•	•	1			
Input Capacitance	C _{iss}				1155	pF	
Output Capacitance	C _{oss}	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$		108			
Reverse Transfer Capacitance	C _{rss}			84			
Gate resistance	R _g	VDS =0V,VGS =0V, f =1MHz			3.6	Ω	
Switching Characteristics ⁽⁴⁾	•	•	•	•			
Turn-on delay time	t _{d(on)}				5		
Turn-on rise time	t _r	V_{GS} =10V, V_{DS} =15V,			7	ns	
Turn-off delay time	t _{d(off)}	$R_L=2.7\Omega,R_{GEN}=3\Omega$			40		
Turn-off fall time	t _f	1			6		
Source-Drain Diode characteristics	•	•	•	•			
Diode Forward voltage ⁽³⁾	V _{SD}	V _{GS} =0V, I _S =1A			1	V	

Notes:

- 1. Repetitive Rating : Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t < 5sec.
- 3. Pulse Test : Pulse Width≤300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production testing.

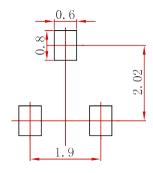


SOT-23-3L Package Outline Dimensions



Symbol	Dimensions I	n Millimeters	Dimensions In Inches	
	Min.	Max.	Min.	Max.
Α	1.050	1.250	0.041	0.049
A1	0	0.150	0.000	0.006
A2	1.050	1.250	0.041	0.049
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	2.650	2.950	0.104	0.116
E1	1.500	1.700	0.059	0.067
е	0.950TYP		0.037	7TYP
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

SOT-23-3L Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

NOTICE

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Date of change	Rev#	revise content
2023/09/02	A/0	/
2023/10/11	A/1	升版规格书